

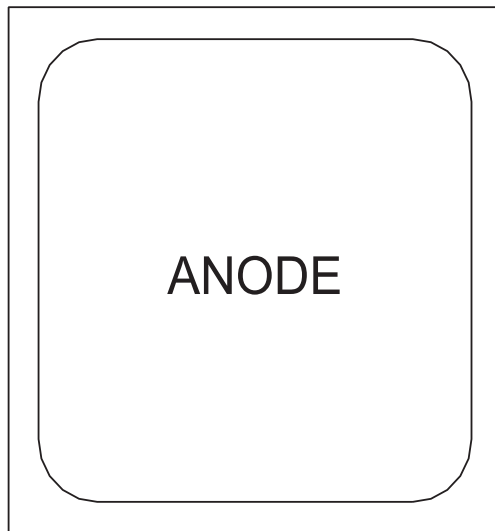
PROCESS CPD18
Ultra Fast Rectifier
8 Amp Glass Passivated Rectifier Chip



PROCESS DETAILS

Process	GLASS PASSIVATED MESA
Die Size	100 x 100 MILS
Die Thickness	14 MILS
Anode Bonding Pad Area	78 x 78 MILS
Top Side Metalization	Ni/Au - 5,000Å/2,000Å
Back Side Metalization	Ni/Au - 5,000Å/2,000Å

GEOMETRY



BACKSIDE CATHODE

R0

GROSS DIE PER 4 INCH WAFER

1,170

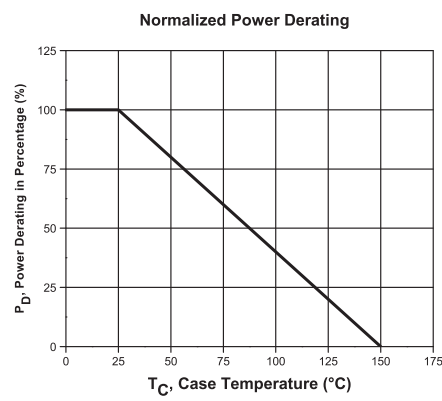
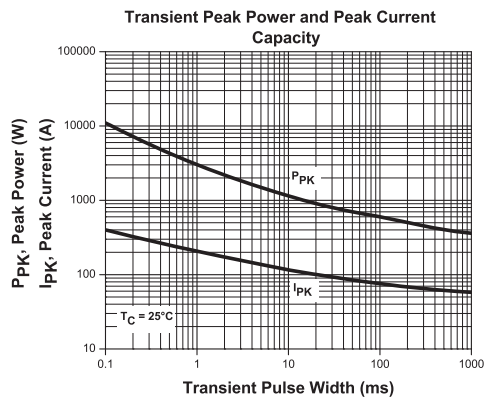
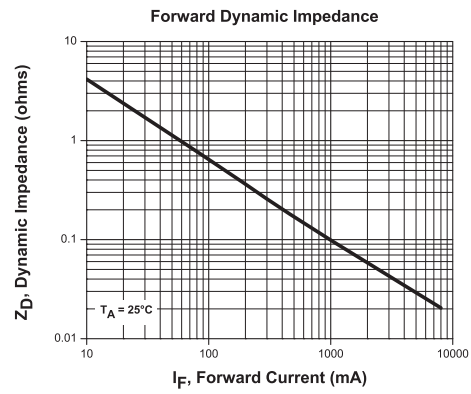
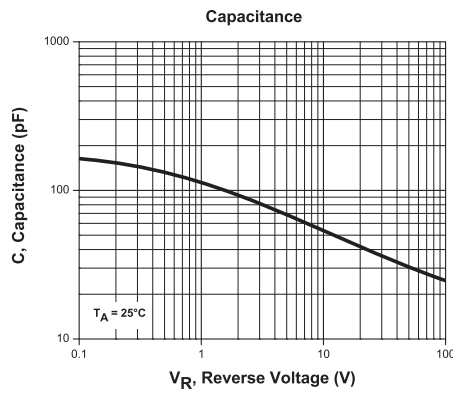
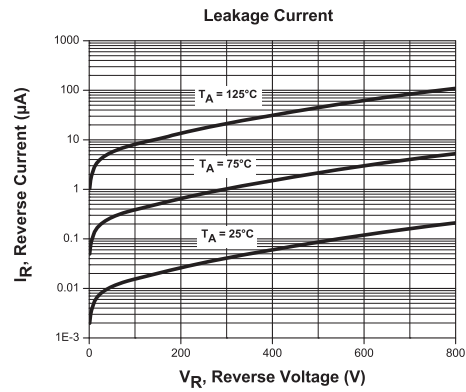
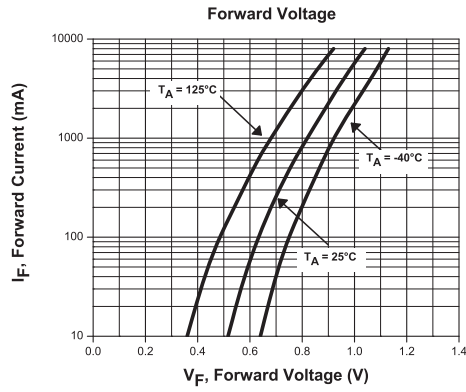
PRINCIPAL DEVICE TYPES

1N5807 thru 1N5811
UES1301 thru UES1306
UES1401 thru UES1403
CUDD8-02 Series

R4 (22-March 2010)

PROCESS CPD18

Typical Electrical Characteristics



R4 (22-March 2010)